

500mA 40V Low VF

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Chip Information

Chip Size	0.68 x 0.68mm
Pad Size	0.57 x 0.57mm
Chip Quantity	23678 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	20	V	
Average Forward Rectified Current	IF(AV)	500	mA	
Peak Forward Surge Current	IFSM	3	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.300	0.280	0.200	V	IF=10mA Ta=25degC
	VF2	0.500	0.485	0.455	V	IF=500mA Ta=25degC
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	30	25	15	uA	VR=10V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	40	44	55	V	IR=500uA
Junction Capacitance	Cj				pF	f=1MHz,VR=10V
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
YJP195	180 +/- 20um	Au(For Eutectic)
YJP197	150 +/- 20um	Au(For Eutectic)
YJP196	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For RB411D